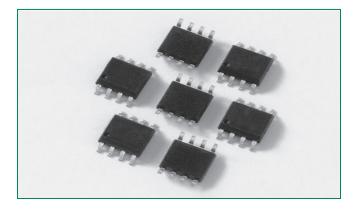


Po

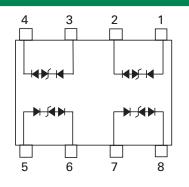
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F RoHS

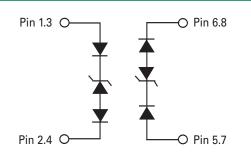
# SPLV2.8-4 Series 2.8V 50A TVS Array



#### Pinout



### **Functional Block Diagram**



## Description

The SPLV2.8-4 was designed to protect low voltage, CMOS devices from ESD and lightning induced transients. There is a compensating diode in series with each low voltage TVS to present a low loading capacitance to the line being protected. These robust structures can safely absorb repetitive ESD strikes at  $\pm 30$ kV (contact discharge) per IEC61000-4-2 standard and each structure can safely dissipate up to 40A (IEC61000-4-5, t<sub>p</sub>=8/20µs) with very low clamping voltages.

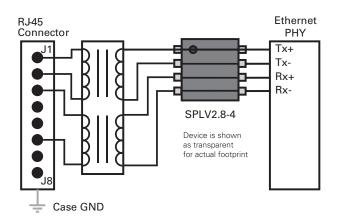
## Features

- ESD, IEC61000-4-2, ±30kV contact, ±30kV air
- EFT, IEC61000-4-4, 40A (5/50ns)
- Lightning, IEC61000-4-5, 40A (8/20µs)
- Low capacitance of 2pF per line
- Low leakage current of 1μA (MAX) at 2.8V
- SOIC-8 pin configuration allows for simple flow-through layout

#### Applications

- 10/100/1000 Ethernet
- Analog InputsBase Stations
- WAN/LAN Equipment
- Switching Systems
- Desktops, Servers, and Notebooks

### **Application Example**



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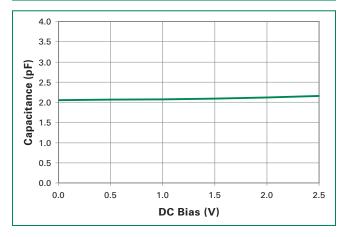
Electrical Characteristics (T <sub>op</sub> = 25°C)						
Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Reverse Standoff Voltage	V <sub>RWM</sub>	I <sub>R</sub> ≤1μA			2.8	V
Reverse Breakdown Voltage	V <sub>BR</sub>	I <sub>τ</sub> =2μA	3.0			V
Snap Back Voltage V <sub>SB</sub>		I <sub>T</sub> =50mA	2.8			V
Reverse Leakage Current	I <sub>leak</sub>	V <sub>R</sub> =2.8V (Each Line)			1	μA
Clamping Voltage <sup>1</sup>	V <sub>c</sub>	I <sub>pp</sub> =5A, t <sub>p</sub> =8/20μs (Each Line)		7.0	8.5	V
Clamping Voltage <sup>1</sup>	V <sub>c</sub>	I <sub>PP</sub> =24A, t <sub>P</sub> =8/20μs (Each Line)		13.9	15.0	V
ESD Withstand Voltage <sup>1</sup>		IEC61000-4-2 (Contact)	±30			kV
	V <sub>ESD</sub>	IEC61000-4-2 (Air)	±30			kV
Dynamic Resistance	R <sub>DYN</sub>	(V <sub>c2</sub> - V <sub>c1</sub> ) / (I <sub>PP2</sub> - I <sub>PP1</sub> ) (Each Line)		0.4		Ω
Diode Capacitance <sup>1</sup> C <sub>D</sub> V <sub>R</sub> =0V, f=1MHz (Each		V <sub>R</sub> =0V, f=1MHz (Each Line)		2.0	2.5	pF

Note: 1Parameter is guaranteed by design and/or device characterization.

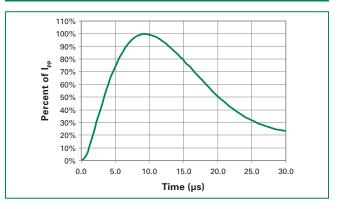
Absolute Maximum Ratings				
Parameter	Rating	Units		
Peak Pulse Power (t <sub>P</sub> =8/20µs)	600	W		
Peak Pulse Current (t <sub>P</sub> =8/20µs)	40	А		
Operating Temperature	-40 to 85	°C		
Storage Temperature	-60 to 150	°C		

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

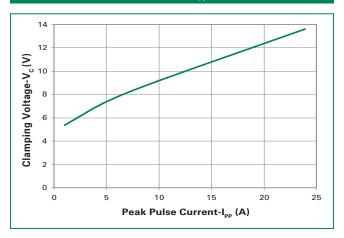
# Figure 1: Capacitance vs. Reverse Voltage



## Figure 3: Pulse Waveform



## Figure 2: Clamping Voltage vs. I<sub>PP</sub>





#### **Product Characteristics**

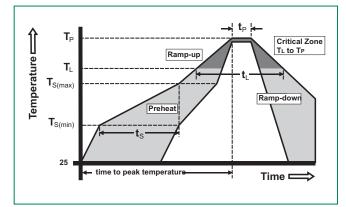
Lead Plating	Matte Tin
Lead Material	Copper Alloy
Lead Coplanarity	0.0004 inches (0.102mm)
Subsitute Material	Silicon
Body Material	Molded Epoxy
Flammability	UL94-V-0

Notes

- All dimensions are in millimeters
- 2. Dimensions include solder plating.
- Dimensions are exclusive of mold flash & metal burr.
  All specifications comply to JEDEC SPEC MO-203 Issue A
  Blo is facing up for mold and facing down for trim/form, i.e. reverse trim/form.
- 6. Package surface matte finish VDI 11-13.

#### **Soldering Parameters**

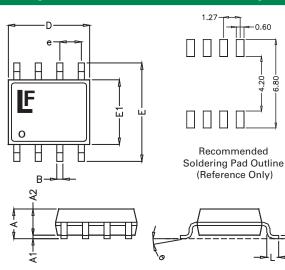
Reflow Condition		Pb – Free assembly	
Pre Heat	-Temperature Min (T <sub>s(min)</sub> )	150°C	
	-Temperature Max (T <sub>s(max)</sub> )	200°C	
	-Time (min to max) (t <sub>s</sub> )	60 – 180 secs	
Average ramp up rate (Liquidus) Temp (T <sub>1</sub> ) to peak		5°C/second max	
T <sub>S(max)</sub> to T <sub>L</sub> - Ramp-up Rate		5°C/second max	
Reflow	-Temperature (T <sub>L</sub> ) (Liquidus)	217°C	
	-Temperature (t <sub>L</sub> )	60 – 150 seconds	
PeakTemperature (T <sub>P</sub> )		250 <sup>+0/-5</sup> °C	
Time within 5°C of actual peak Temperature (t <sub>n</sub> )		20 – 40 seconds	
Ramp-down Rate		5°C/second max	
Time 25°C to peak Temperature (T <sub>P</sub> )		8 minutes Max.	
Do not exceed		260°C	



#### Package Dimensions — Mechanical Drawings and Recommended Solder Pad Outline

0.60

.20 6.80



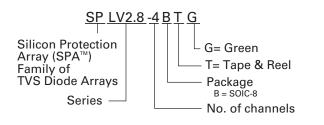


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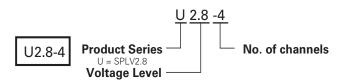
SPLV2.8-4 Series



#### Part Numbering System



#### Part Marking System



**Ordering Information** 

Part Number	Package	Marking	Min. Order Qty.
SPLV2.8-4BTG	SOIC-8	U2.8-4	2500

#### Embossed Carrier Tape & Reel Specification - SOIC Package

